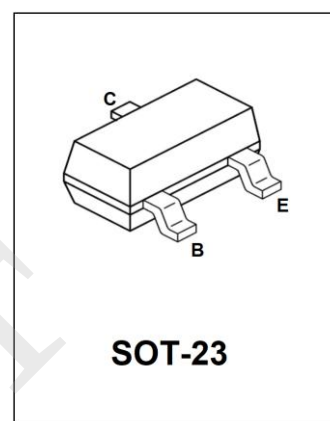


MMBT5401

- Complementary to: MMBT5551
- Package: SOT-23

Maximum Ratings (Ta = 25°)

Parameter	Symbol	Rating	Unit
Collector-base voltage	BV _{CBO}	-180	V
Collector-emitter voltage	BV _{CEO}	-160	V
Emitter-base voltage	BV _{EBO}	-6	V
Collector current	I _{CM}	-600	mA
Collector Power Dissipation	P _C	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C



Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100 μA, I _E =0	-180			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-1mA, I _B =0	-160			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100 μA, I _C =0	-6			V
collector-base cut-off current	I _{CBO}	V _{CB} =-160V, I _E =0			-0.1	μA
collector-emitter cut-off current	I _{CEO}	V _{CE} =-140V, I _B =0			-0.1	μA
emitter-base cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	H _{FE1}	V _{CE} =-5V, I _B =-1mA	80			
	H _{FE2}	V _{CE} =-5V, I _B =-10mA	80		300	
	H _{FE3}	V _{CE} =-5V, I _B =-50mA	30			
collector-emitter saturation voltage	V _{CESAT}	I _C =-50mA, I _B =-5mA			0.25	V
Base-Emitter Saturation Voltage	V _{BESAT}	I _C =-50mA, I _B =-5mA			1.2	V
Transition frequency	f _T	V _{CE} =-10V, I _B =-10mA	100			MHz

Classification of H_{FE}

Rank	MMBT5401-O	MMBT5401-A	MMBT5401-B
Range	80-100	100-200	200-300